

RF Power MOSFET Transistor 5 W, 500 - 1000 MHz, 28 V

Rev. V1

Features

- N-Channel enhancement mode device
- DMOS structure
- · Lower capacitances for broadband operation
- Common source configuration
- Lower noise floor
- Applications

Broadband linear operation 500 MHz to 1400 MHz

RoHS Compliant

Absolute Maximum Ratings @ 25°C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	65	V
Gate-Source Voltage	V_{GS}	20	V
Drain-Source Current	I _{DS}	1.4	Α
Power Dissipation	P_D	14.4	W
Junction Temperature	TJ	200	°C
Storage Temperature	T _{STG}	-65 to +150	°C
Thermal Resistance	θ _{JC}	12.1	°C/W

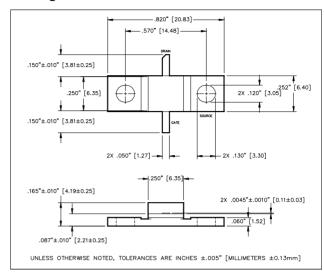
Typical Device Impedance

F (MHz)	Z _{IN} (Ω)	Z _{LOAD} (Ω)		
500	4.3 - j29.0	27.3 +j28.6		
1000	2.2 - j2.75	8.0 + j16.0		
1400 2.8 - j3.0 9.4 + j10.6				
V_{DD} = 28V, I_{DQ} = 50mA, P_{OUT} = 5.0 W				

 $Z_{\mbox{\scriptsize IN}}$ is the series equivalent input impedance of the device from gate to source.

 Z_{LOAD} is the optimum series equivalent load impedance as measured from drain to ground.

Package Outline



LETTER	MILLIM	ETERS	INCHES		
DIM.	MIN	MAX	MIN	MAX	
Α	20.70	20.96	.815	.825	
В	14.35	14.61	.565	.575	
С	13.72	14.22	.540	.560	
D	6.27	6.53	.247	.257	
Е	6.22	6.48	.245	.255	
F	6.22	6.48	.245	.255	
G	1.14	1.40	.045	.055	
Н	2.92	3.18	.115	.125	
J	1.40	1.65	.055	.065	
K	1.96	2.46	.077	.097	
L	3.61	4.37	.142	.172	
М	.08	.15	.003	.006	

Electrical Characteristics @ 25°C

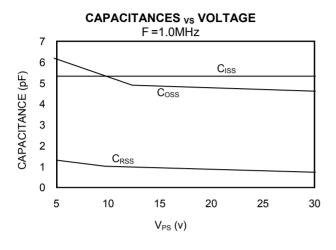
Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	65	-	٧	$V_{GS} = 0.0 \text{ V}$, $I_{DS} = 2.0 \text{ mA}$
Drain-Source Leakage Current	I _{DSS}	1	1.0	mA	$V_{GS} = 28.0 \text{ V}$, $V_{GS} = 0.0 \text{ V}$
Gate-Source Leakage Current	I _{GSS}	-	1.0	μΑ	V _{GS} = 20.0 V , V _{DS} = 0.0 V
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	٧	$V_{DS} = 10.0 \text{ V}$, $I_{DS} = 10.0 \text{ mA}$
Forward Transconductance	G _M	80	-	mS	V_{DS} = 10.0 V , I_{DS} = 100.0 mA , Δ V_{GS} = 1.0V, 80 μ s Pulse
Input Capacitance	C _{ISS}	-	7	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Output Capacitance	Coss	-	5	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C _{RSS}	-	2.4	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Power Gain	G₽	10	-	dB	V_{DD} = 28.0 V, I_{DQ} = 50 mA, P_{OUT} = 5.0 W F =1.0 GHz
Drain Efficiency	ŋ _D	50	-	%	V_{DD} = 28.0 V, I_{DQ} = 50 mA, P_{OUT} = 5.0 W F =1.0 GHz
Load Mismatch Tolerance	VSWR-T	-	20:1	-	V_{DD} = 28.0 V, I_{DQ} = 50 mA, P_{OUT} = 5.0 W F =1.0 GHz

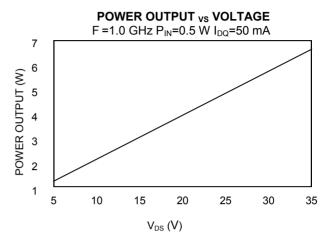


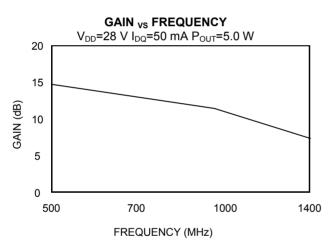
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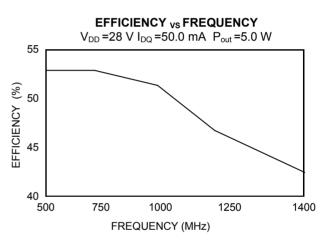
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Typical Broadband Performance Curves









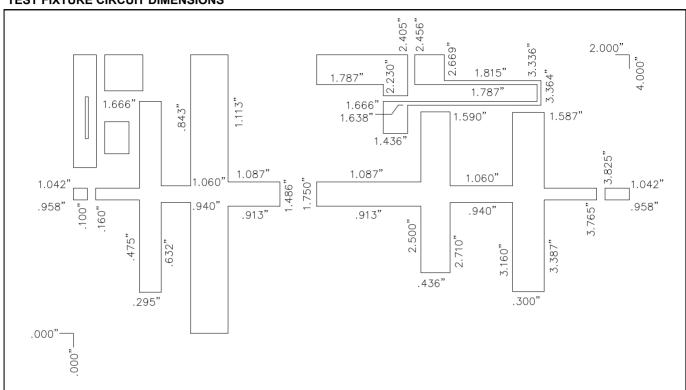
POWER OUTPUT vs POWER INPUT $V_{DD} = 28 \text{ V } I_{DO} = 50 \text{ mA}$ 7 1000 MHz 500MHz 6 POWER OUTPUT (W) 5 4 3 2 0 0 0.05 0.2 0.4 0.6 8.0 1 POWER INPUT (W)



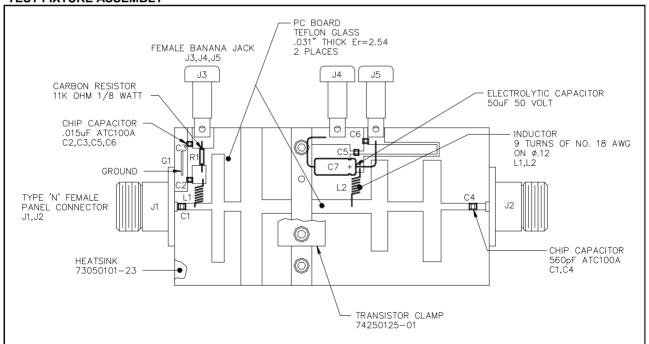
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TEST FIXTURE CIRCUIT DIMENSIONS



TEST FIXTURE ASSEMBLY



LF2805A



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